BFL4026

ON Semiconductor®

N-Channel Power MOSFET 900V, 5A, 3.6 Ω , TO-220F-3FS

http://onsemi.com

Features

- ON-resistance RDS(on)= 2.8Ω (typ.)
- · 10V drive

• Input capacitance Ciss=650pF (typ.)

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		900	V
Gate-to-Source Voltage	VGSS		±30	V
Desir Courset (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	5	А
Drain Current (DC)	I _{Dpack} *2	Tc=25°C (Our ideal heat dissipation condition)*3	3.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	10	Α
Allowable Power Dissipation	Do		2.0	W
	PD	Tc=25°C (Our ideal heat dissipation condition)*3	35	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		132	mJ
Avalanche Current *5	IAV		5	Α

Note: *1 Shows chip capability

- *2 Package limited
- *3 Our condition is radiation from backside.

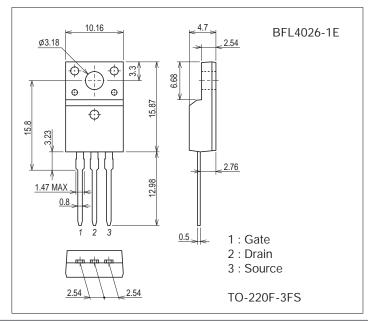
The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- *4 VDD=50V, L=10mH, IAV=5A (Fig.1)
- *5 L≤10mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7528-001



Product & Package Information

• Package : TO-220F-3FS

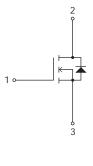
• JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./magazine

Marking

Electrical Connection





Semiconductor Components Industries, LLC, 2013

July, 2013

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Parameter	Symbol Conditions		min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	900			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =720V, V _{GS} =0V			1.0	mA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.0		4.0	V
Forward Transfer Admittance	yfs	VDS=20V, ID=2.5A	1.4	2.8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =2.5A, V _G S=10V		2.8	3.6	Ω
Input Capacitance	Ciss			650		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		100		pF
Reverse Transfer Capacitance	Crss			35		pF
Turn-ON Delay Time	t _d (on)			14		ns
Rise Time	t _r	Con Fig 2		37		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		117		ns
Fall Time	tf			39		ns
Total Gate Charge	Qg			33		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =5A		5.3		nC
Gate-to-Drain "Miller" Charge	Qgd			16.5		nC
Diode Forward Voltage	V _{SD}	IS=5A, VGS=0V		0.85	1.2	V
Reverse Recovery Time	t _{rr}	See Fig.3		720		ns
Reverse Recovery Charge	Q _{rr}	I _S =5A, V _G S=0V, di/dt=100A/μs		4700		nC

Fig.1 Avalanche Resistance Test Circuit

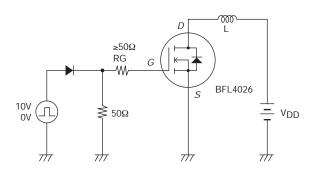


Fig.3 Reverse Recovery Time Test Circuit

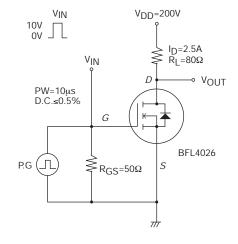
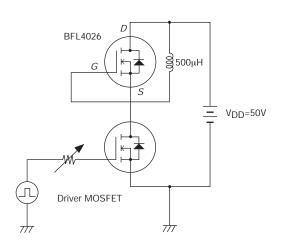
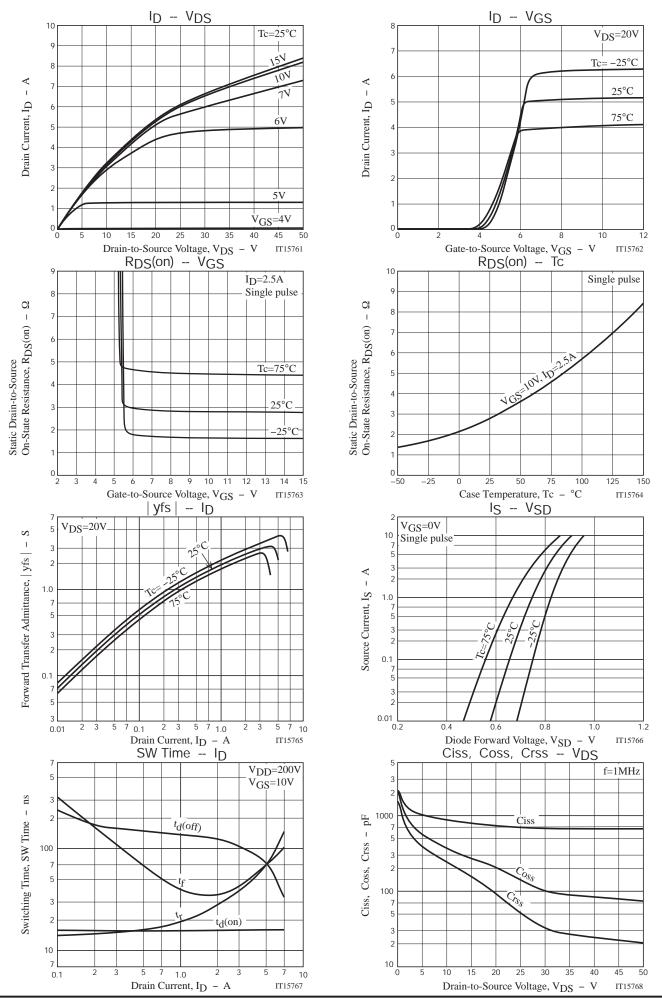


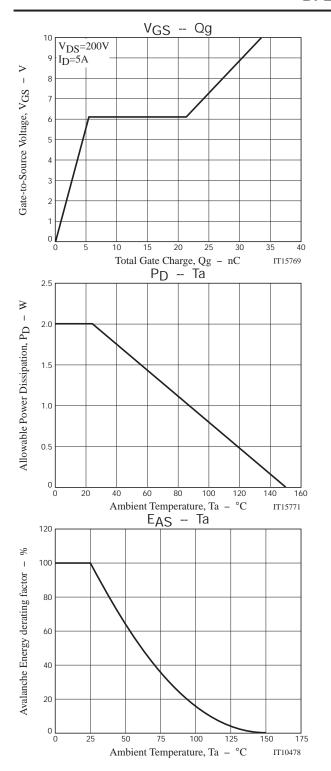
Fig.2 Switching Time Test Circuit

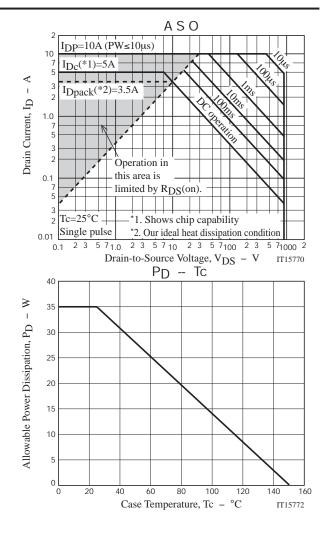


Ordering Information

Device	Package	Shipping	memo
BFL4026-1E	TO-220F-3FS	50pcs./magazine	Pb Free





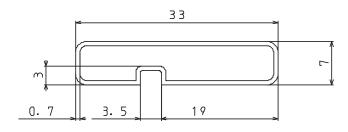


Magazine Specification

BFL4026-1E

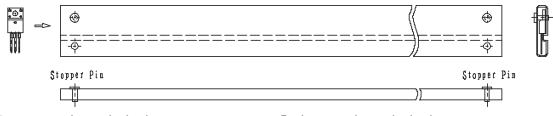
1. Packing Format

Package Name	Magazine Name	Maximum Number of devices contained (po			Packing format		
1 4 4 4 4 4 1 4 4 4 4	Idag as the Hams	l	Inner box	Outer box	Inner BOX	Outer BOX	
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178	

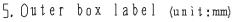


Tolerance=±0, 3mm
Thickness=0, 7±0, 2mm
Length =532, 5±2mm
Material =PVC (Antistatic treatment)

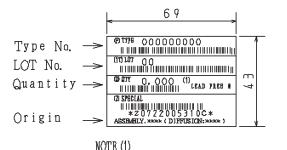
3. Storage method to magazine

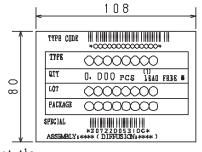


4. Inner box label (unit:mm)



It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



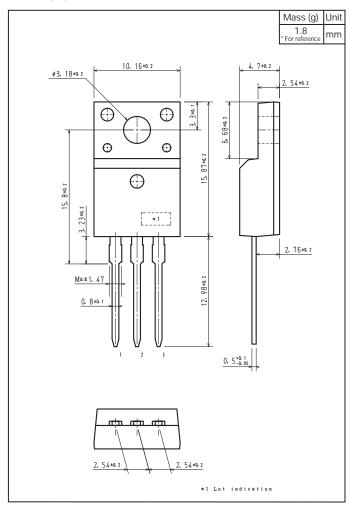


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase			
LEAD FREE	3	JEITA Phase 3A			

Outline Drawing

BFL4026-1E



Note on usage: Since the BFL4026 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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